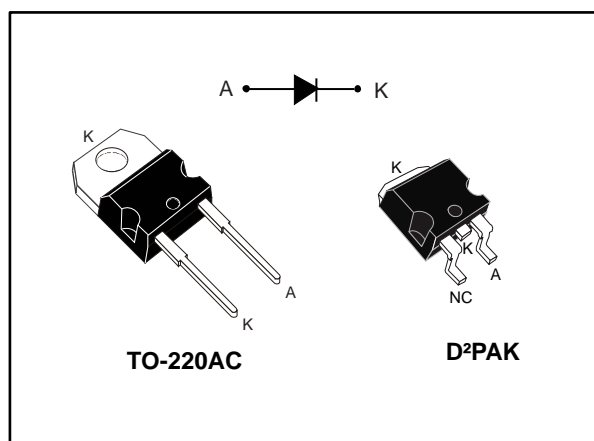


Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

Features

- AEC-Q101 qualified
- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- PPAP capable
- Operating T_j from $-40\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$
- ECOPACK[®]2 compliant component



Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	10 A
V_{RRM}	650 V
T_j (max.)	175 $^\circ\text{C}$
V_F (typ.)	1.30 V

1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage	T_j from -40 °C to 175 °C	650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	$T_c = 150$ °C ⁽¹⁾ , DC current	10	A
I_{FRM}	Repetitive peak forward current	$T_c = 150$ °C, $T_j = 175$ °C, $\delta = 0.1$	42	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal, $T_c = 25$ °C	48	A
		$t_p = 10$ ms sinusoidal, $T_c = 125$ °C	39	
		$t_p = 10$ μ s square, $T_c = 25$ °C	210	
T_{stg}	Storage temperature range		-65 to +175	°C
T_j	Operating junction temperature ⁽²⁾		-40 to +175	°C

Notes:

⁽¹⁾Value based on $R_{th(j-c)}$ max.

⁽²⁾ $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal parameters

Symbol	Parameter	Value		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Junction to case	1.0	1.5	°C/W

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25$ °C	$V_R = V_{RRM}$	-	7	130	μ A
		$T_j = 150$ °C		-	53	900	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25$ °C	$I_F = 10$ A	-	1.30	1.45	V
		$T_j = 150$ °C		-	1.45	1.65	
		$T_j = 175$ °C		-	1.50		

Notes:

⁽¹⁾Pulse test: $t_p = 5$ ms, $\delta < 2\%$

⁽²⁾Pulse test: $t_p = 500$ μ s, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 0.97 \times I_{F(AV)} + 0.068 \times I_{F(RMS)}^2$$

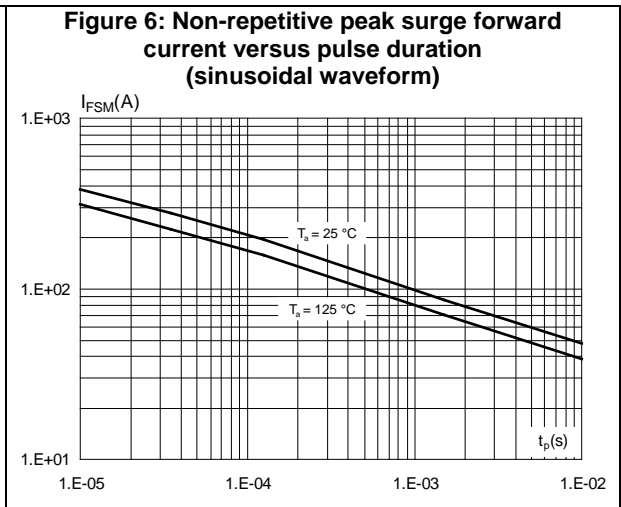
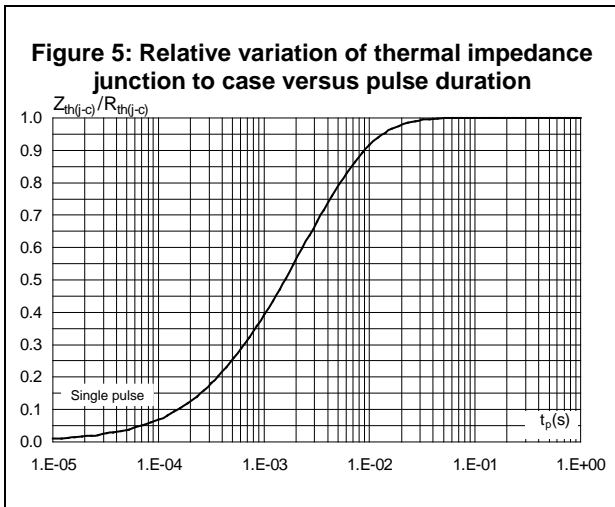
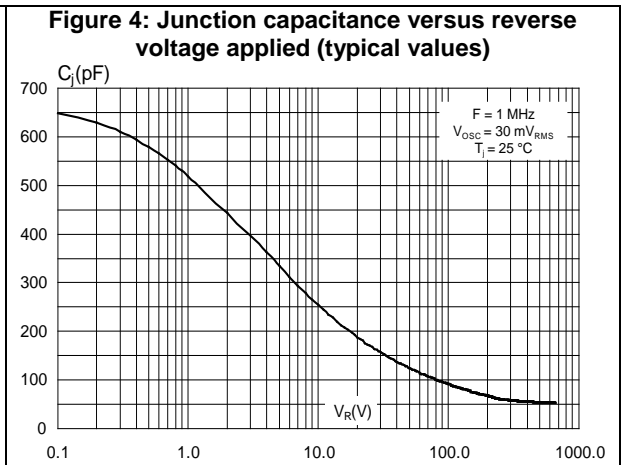
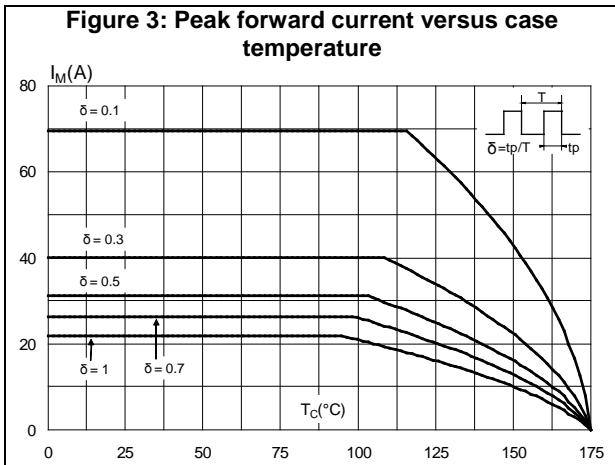
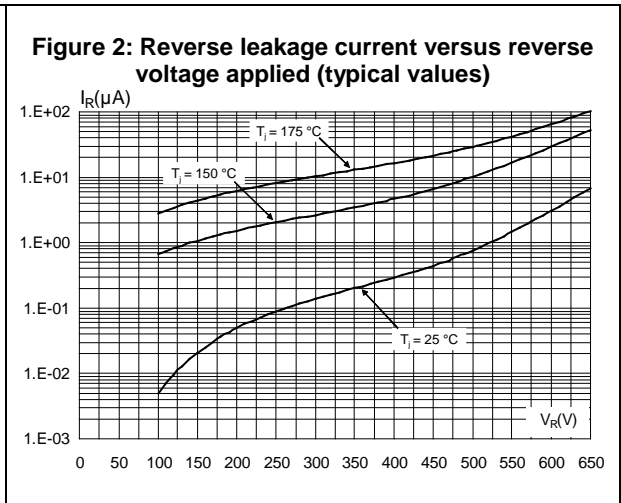
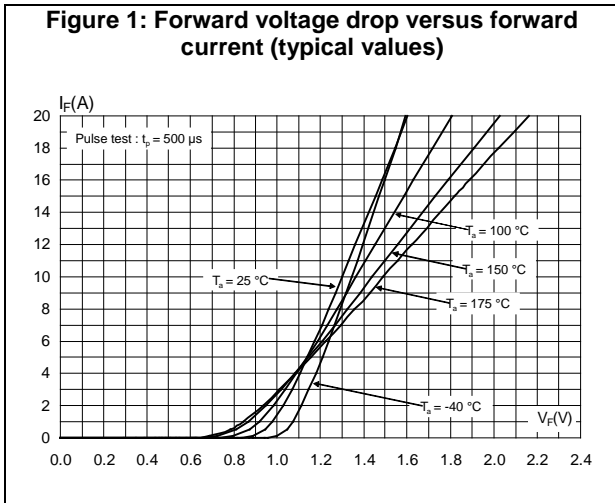
Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{Cj}^{(1)}$	Total capacitive charge	$V_R = 400 \text{ V}$	34	nC
C_j	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	670	pF
		$V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	55	

Notes:

⁽¹⁾Most accurate value for the capacitive charge: $Q_{Cj}(V_R) = \int_0^{V_R} C_j(V) dV$

1.1 Characteristics (curves)



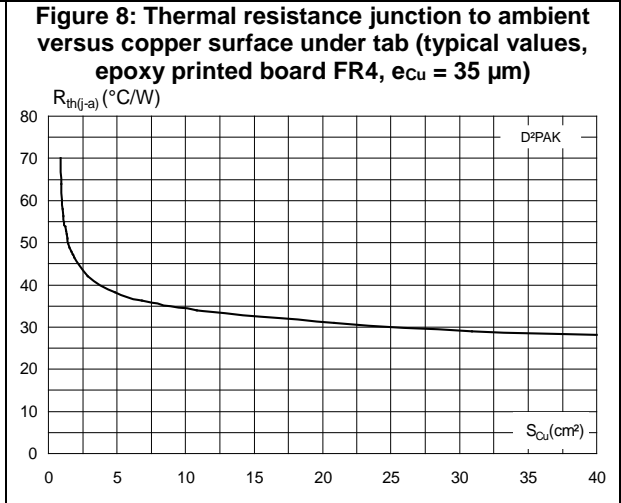
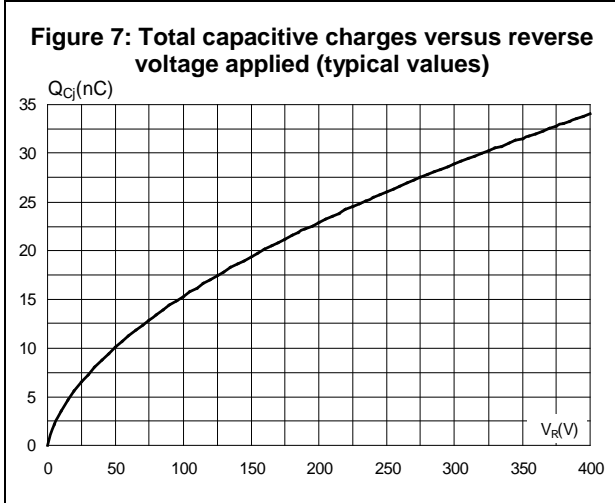


Table 6: TO-220AC package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
ØI	3.75	3.85	0.147	0.151

2.2 D²PAK package information

Figure 10: D²PAK package outline

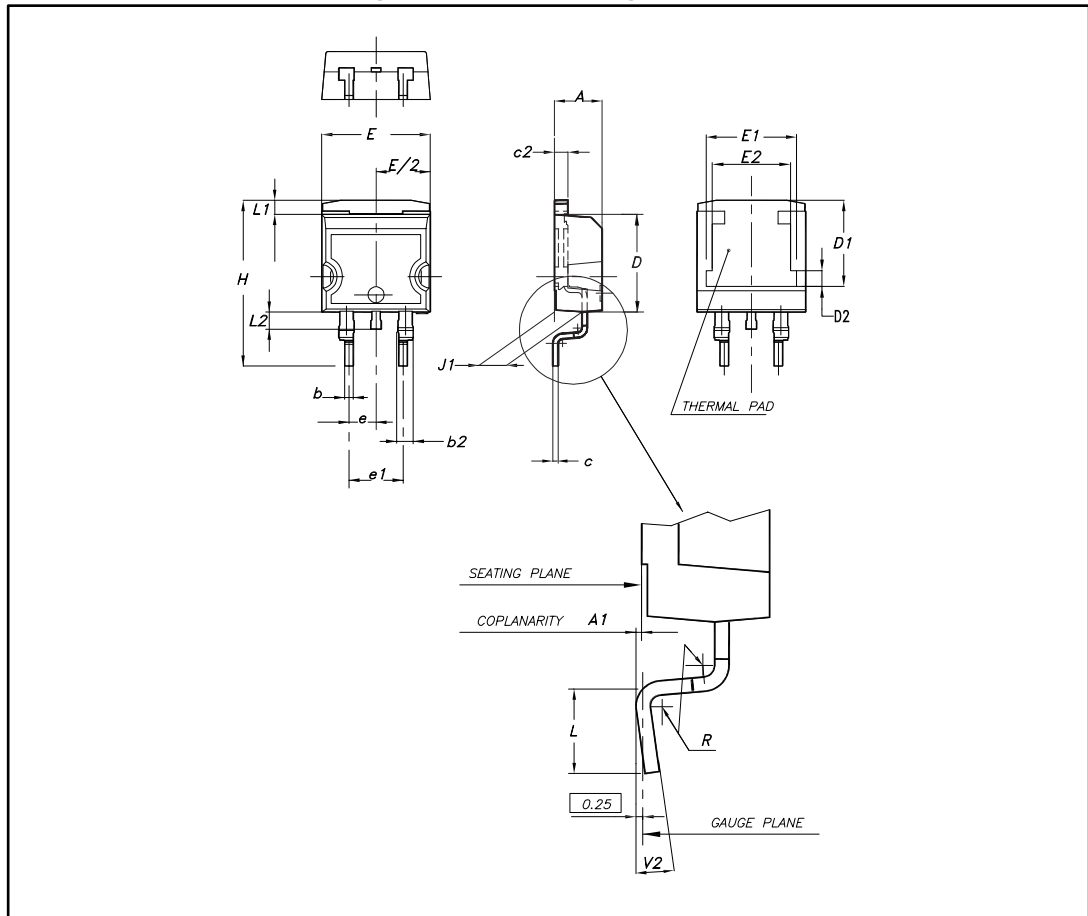
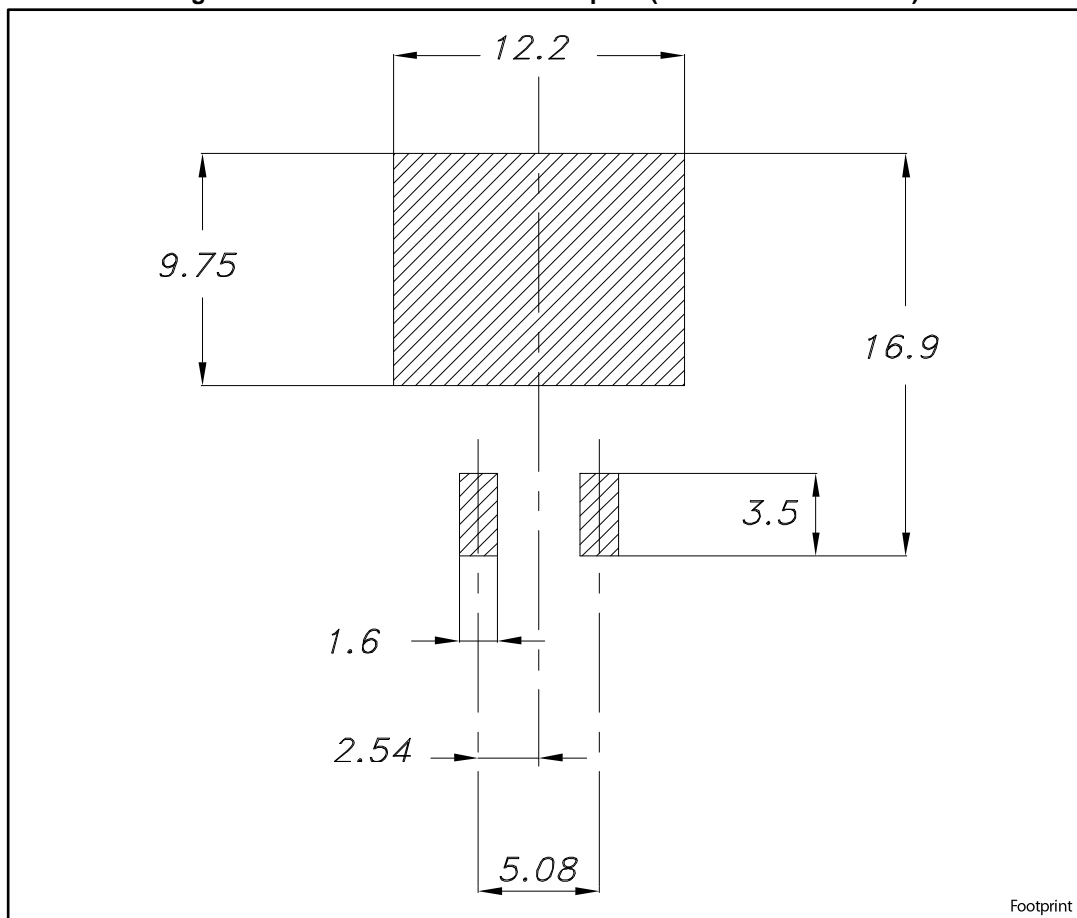


Table 7: D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409
E1	8.50	8.70	8.90	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

Figure 11: D²PAK recommended footprint (dimensions are in mm)



3 Ordering information

Table 8: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10065DY	PSC10065DY	TO-220AC	1.86 g	50	Tube
STPSC10065GY-TR	PSC10065GY	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 9: Document revision history

Date	Revision	Changes
13-Jun-2017	1	First issue.
18-Jul-2017	2	Updated <i>Table 4: "Static electrical characteristics"</i> .
09-Nov-2017	3	Added D ² PAK package.

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